

# P-Channel 60-V (D-S) MOSFET

#### **Features**

- · Low rDS(on) trench technology
- · Low thermal impedance
- · Fast switching speed
- · Low thermal impedance copper lead frame

### DFN5X6-8L saves board space

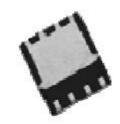
· RoHS compliant package

#### **Typical Applications:**

- · White LED boost converters
- · Automotive Systems
- · Industrial DC/DC Conversion Circuits

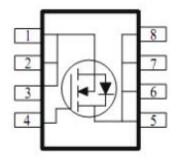
#### **Packing & Order Information**

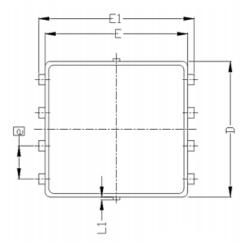
3,000/Reel

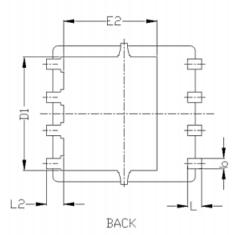


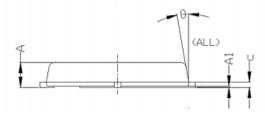
RoHS COMPLIANT

#### **Graphic symbol**









SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES			
SIMBOLS	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.85	0.95	1.00	0.033	0.037	0.039	
Al	0.00		0.05	0.000		0.002	
b	0.30	0.40	0.50	0.012	0.016	0.020	
c	0.15	0.20	0.25	0.006	0.008	0.010	
D	5. 20 BSC			0, 205 BSC			
D1	4. 35 BSC			0. 171 BSC			
E	5, 55 BSC			0. 219 BSC			
E1	6. 05 BSC			0. 238 BSC			
E2	3. 62 BSC			0. 143 BSC			
e	1. 27 BSC			0. 050 BSC			
L	0.45	0.55	0.65	0.018	0.022	0.026	
L1	0		0.15	0		0.006	
L2	0.68 REF			0. 027 REF			
θ	0°		10°	0° 10°			



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### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings (T <sub>A</sub> =25°C unless otherwise specified)						
Symbol	Parameter	Value	Unit			
$V_{DS}$	Drain-Source Voltage	60	V			
V <sub>GS</sub>	Gate-Source Voltage ±20					
I <sub>D</sub>	Continuous Drain Current <sup>a</sup> (T <sub>A</sub> =25°C)	13	А			
	Continuous Drain Current <sup>a</sup> (T <sub>A</sub> =70°C)	11	Α			
I <sub>DM</sub>	Pulsed Drain Current <sup>b</sup>	50	А			
I <sub>S</sub>	Continuous Source Current (Diode Conduction) <sup>a</sup>	4.6	А			
P <sub>D</sub>	Power Dissipation <sup>a</sup> (T <sub>A</sub> =25°C)	5	W			
	Power Dissipation <sup>a</sup> (T <sub>A</sub> =70°C)	3.2	W			
T <sub>J</sub> /T <sub>STG</sub>	Operating Junction and Storage Temperature	-55 to +150	°C			

Thermal Resistance Ratings						
Symbol	Parameter	Maximum	Units			
$R_{ heta JA}$	Maximum Junction-to-Ambient <sup>a</sup> (t <= 10 sec)	25	°C/W			
	Maximum Junction-to-Ambient <sup>a</sup> (Steady-State)	65	C/VV			

#### **Notes**

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Static						
Symbol	Parameter	Test Conditions	Min	Тур.	Max.	Units
$V_{GS(th)}$	Gate-Source Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	1			V
I <sub>GSS</sub>	Gate-Body Leakage	$V_{DS} = 0 \text{ V}$ , $V_{GS} = \pm 20 \text{ V}$			±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			1 25	uA
I <sub>D(on)</sub>	On-State Drain Current	V <sub>DS</sub> = 5 V, V <sub>Gs</sub> = 10 V	25			Α
r DS(on)	Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_D = 10.4 \text{ A}$ $V_{GS} = 4.5 \text{ V}, I_D = 7.2 \text{ A}$			22 26	mΩ
<b>g</b> fs	Forward Tranconductance	V <sub>GS</sub> = 15 V, I <sub>D</sub> = 10.4 A		20		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> = 2.3 A , V <sub>GS</sub> = 0 V		0.7		V



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Dynamic							
Symbol	Parameter	Test Conditions	Min	Тур.	Max.	Units	
$Q_g$	Total Gate Charge	$V_{DS} = 30 \text{ V}, I_{D} = 10.4 \text{ A},$ $V_{GS} = 4.5 \text{ V}$		20		nC	
Q <sub>gs</sub>	Gate-Source Charge			5.8		nC	
$Q_{gd}$	Gate-Drain Charge			10		nC	
t <sub>d(on)</sub>	Turn-On Delay Time	$I_{D} = 10.4 \text{ A}, R_{L} = 2.9 \Omega,$ $V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$ $V_{DS} = 30 \text{ V}$		10		ns	
t <sub>r</sub>	Rise Time			24		ns	
t <sub>d(off)</sub>	Turn-Off Delay Time			67		ns	
tf	Fall Time			37		ns	
C <sub>ISS</sub>	Input Capacitance	$V_{DS} = 15 \text{ V}$ $f = 1 \text{ MHz }, V_{GS} = 0 \text{ V}$		2086		pF	
Coss	Output Capacitance			174		pF	
C <sub>RSS</sub>	Reverse Transfer Capacitance			160		pF	

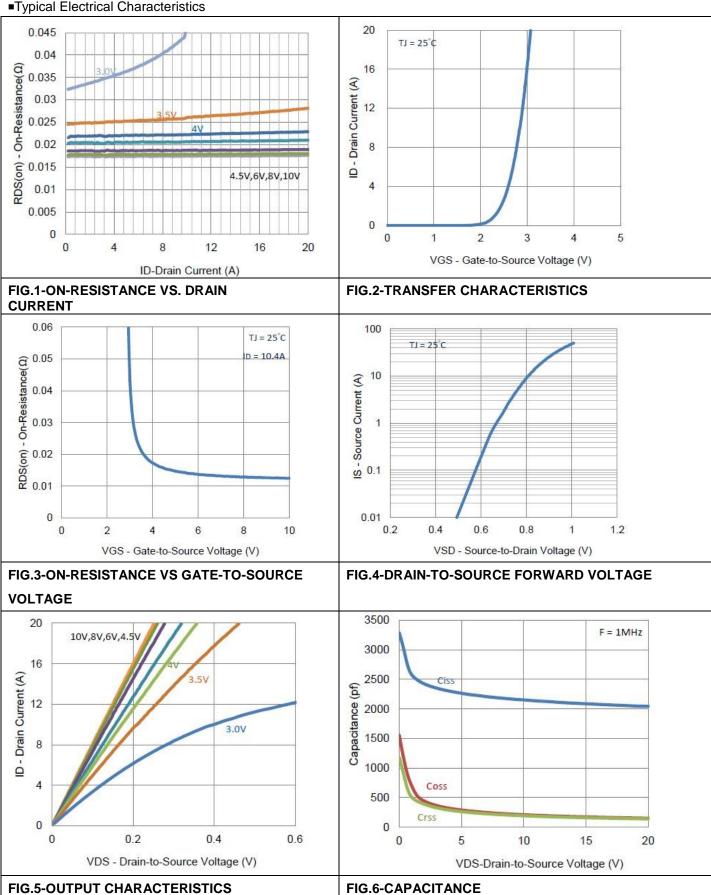
#### **Notes**

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.



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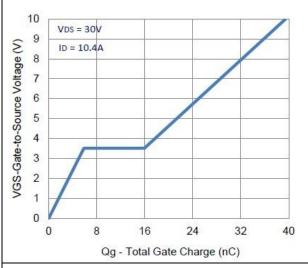
■Typical Electrical Characteristics

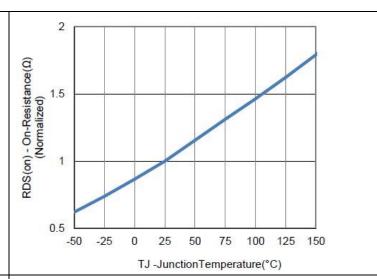




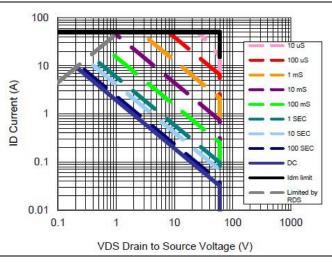
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#### ■Typical Electrical Characteristics

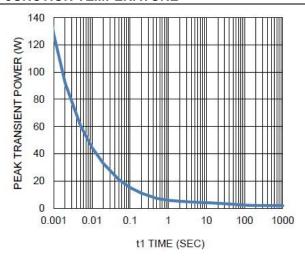




#### FIG.7-GATE CHARGE



# FIG.8-NORMALIZED ON-RESISTANCE VS JUNCTION TEMPERATURE



#### FIG.9-SAFE OPERATIING AREA



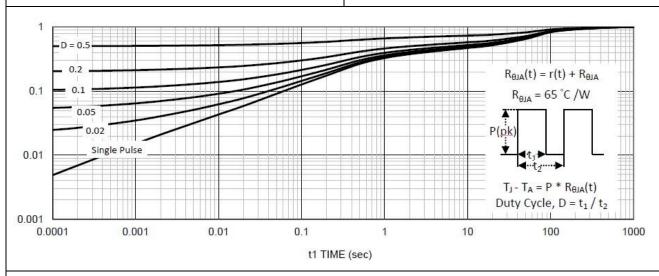


FIG.11-NORMALIZED THERMAL TRANSIENT JUNCTION TO AMBIENT



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